

VE311 Electronic Circuit Homework 5

Due: June 19th

Note:

- 1) Please use A4 size paper or page.
- 2) Please clearly state out your final result for each question.
- 3) Please attach the screenshot of Pspice simulation result if necessary.

Question 1. Common Gate (Easy)

In the common gate stage amplifier, the internal resistance of I is $1k\Omega$, what is the output resistance when $I_{REF} = 0.01mA$ and $0.1mA$ respectively? (Neglect body effect)

Parameter for NMOS: $V_{THN} = 0.7V$, $K_n = 110\mu A/V^2$, $\lambda = 0.04V^{-1}$

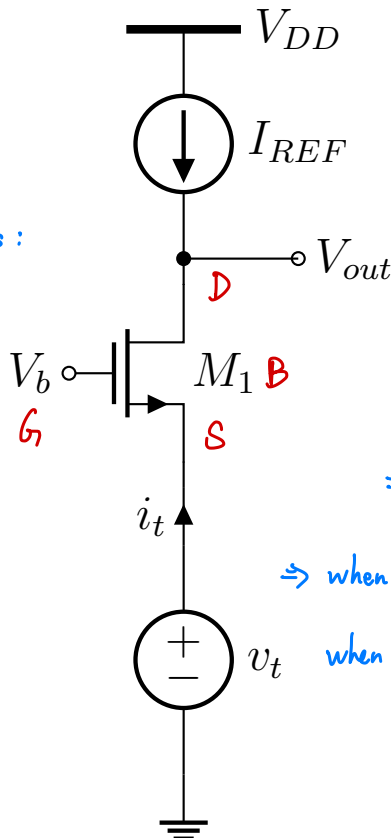
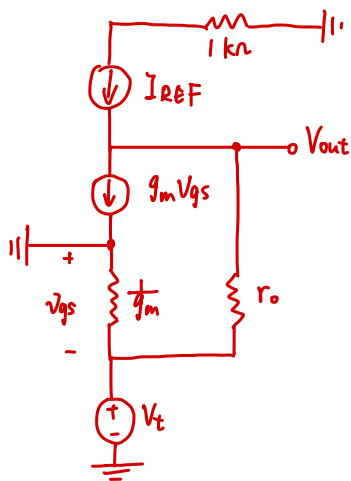
Parameter for PMOS: $V_{THP} = -0.7V$, $K_p = 50\mu A/V^2$, $\lambda = 0.05V^{-1}$

All the size of transistor is $W = 20\mu m$, $L = 1\mu m$

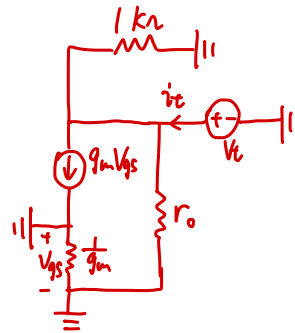
Transconductance $g_m = \sqrt{2K_n' \frac{W}{L} I_D}$

Output Resistance $r_o = \frac{1}{\lambda I_D}$

Then we do the small signal analysis:



To find the output resistance, we just need to analyze the following circuit:



$$\Rightarrow R_{out} = 1k\Omega \parallel r_o$$

$$\Rightarrow \text{when } I_D = 0.1mA, R_{out} = \frac{1}{\lambda \cdot 0.1 \times 10^{-3}} \parallel (1k) = 996.02\Omega$$

$$\text{when } I_D = 0.01mA, R_{out} = \frac{1}{\lambda \cdot 0.01 \times 10^{-3}} \parallel (1k) = 999.60\Omega$$

Question 2. Common Gate Common Source (Medium)

Find the intrinsic gain A_v and output impedance R_{out} for the amplifier when $I_1 = 0.01$ and 0.1 mA respectively. (Neglect body effect)

Parameter for NMOS: $V_{THN} = 0.7 \text{ V}$, $K_n = 110 \mu\text{A}/\text{V}^2$, $\lambda = 0.04 \text{ V}^{-1}$

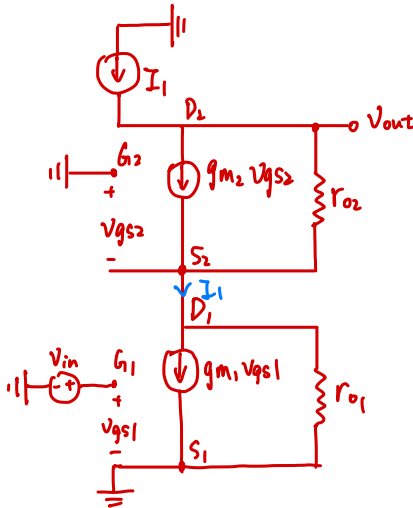
Parameter for PMOS: $V_{THP} = -0.7 \text{ V}$, $K_p = 50 \mu\text{A}/\text{V}^2$, $\lambda = 0.05 \text{ V}^{-1}$

All the size of transistor is $W = 20 \mu\text{m}$, $L = 1 \mu\text{m}$

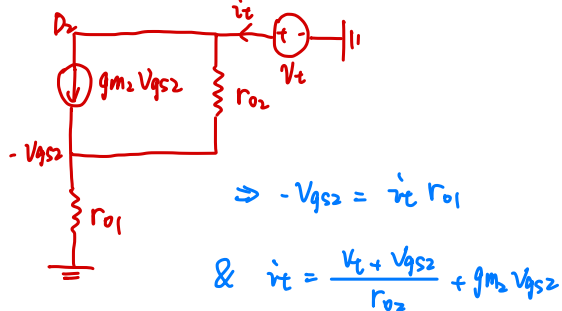
Transconductance $g_m = \sqrt{2k'_n \frac{W}{L} I_D}$

Output Resistance $r_o = \frac{1}{\lambda I_D}$

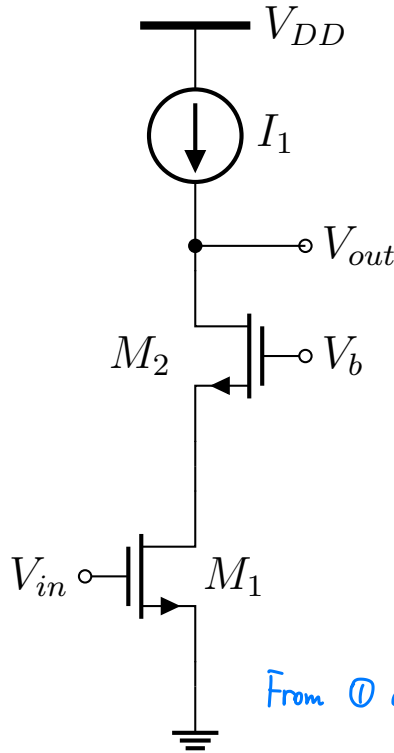
Small signal analysis:



To find the output resistance:



$$\Rightarrow \frac{V_t}{i_t} = R_{out} = r_{o1} + r_{o2} + g_{m2} r_{o1} r_{o2} \quad (1)$$



To get A_v , we need to know $\frac{\partial V_{out}}{\partial V_{in}}$
we can use the AC circuit to obtain the relationship between v_{out} and v_{in}

$$\begin{cases} V_{out} = -V_{gs2} + r_{o2} (I_1 - g_{m2} V_{gs2}) \\ 0 = -V_{gs2} - (I_1 - g_{m1} V_{gs1}) \cdot r_{o1} \\ V_{gs1} = V_{in} \end{cases}$$

$$\Rightarrow V_{out} = V_{in} \cdot - (r_{o1} g_{m1} + r_{o2} r_{o1} g_{m1} g_{m2}) + (r_{o1} + r_{o2} + r_{o1} r_{o2} g_{m2}) I_1$$

$$\Rightarrow A_v = \frac{\partial V_{out}}{\partial V_{in}} = -r_{o1} g_{m1} - r_{o1} r_{o2} g_{m1} g_{m2} \quad (2)$$

From (1) and (2), we can know that

when $I_1 = 0.01 \text{ mA}$, $r_{o1} = r_{o2} = \frac{1}{\lambda I_1} = 2.5 \times 10^6 \Omega$

$$g_{m1} = g_{m2} = \sqrt{2k'_n \frac{W}{L} I_1} = 2.098 \times 10^{-4} \text{ A/V}$$

$$\Rightarrow R_{out} = 1.32 \times 10^9 \Omega, \quad A_v = -2.76 \times 10^5$$

when $I_1 = 0.1 \text{ mA}$, $r_{o1} = r_{o2} = 2.5 \times 10^5 \Omega$

$$g_{m1} = g_{m2} = \sqrt{2k'_n \frac{W}{L} I_1} = 6.633 \times 10^{-4} \text{ A/V}$$

$$\Rightarrow R_{out} = 4.196 \times 10^7 \Omega, \quad A_v = -2.77 \times 10^4$$

Question 3. Common Gate Common Source (Medium)

Find the intrinsic gain A_v and output impedance R_{out} for the amplifier when $I_1 = 0.01$ and $0.1mA$ respectively. (Neglect body effect)

Parameter for NMOS: $V_{THN} = 0.7V$, $K_n = 110\mu A/V^2$, $\lambda = 0.04V^{-1}$

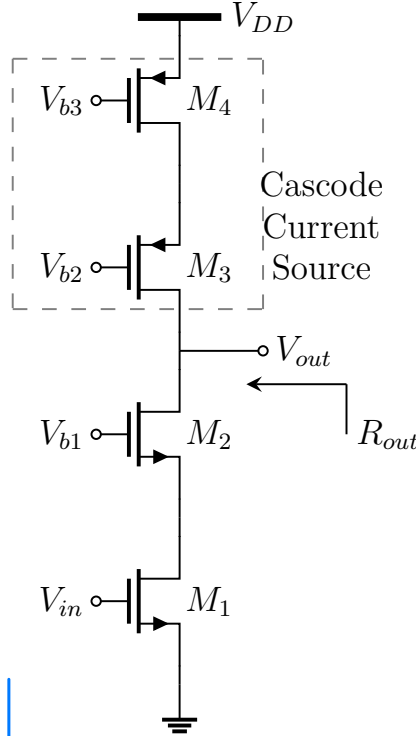
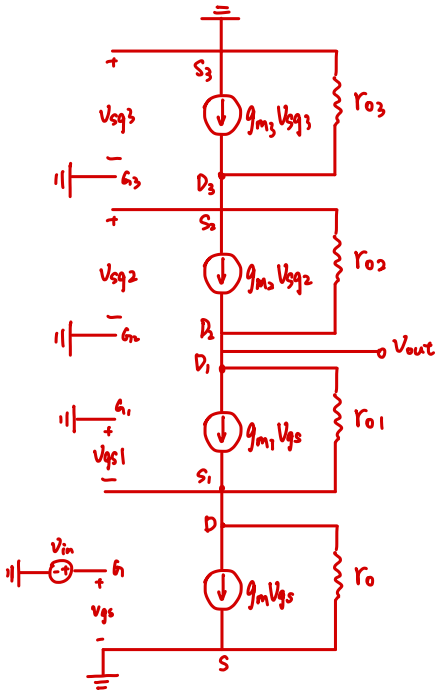
Parameter for PMOS: $V_{THP} = -0.7V$, $K_p = 50\mu A/V^2$, $\lambda = 0.05V^{-1}$

All the size of transistor is $W = 20\mu m$, $L = 1\mu m$

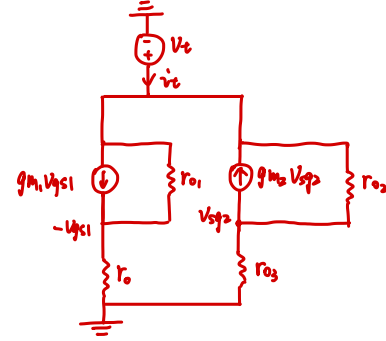
Transconductance $g_{m1} = \sqrt{2k'_n \frac{W}{L} I_D}$
 $g_{m2} = \sqrt{2k'_p \frac{W}{L} I_D}$

Output Resistance $r_o = \frac{1}{\lambda I_D}$

Small signal analysis:



To find the output resistance:



$$\Rightarrow \begin{cases} \frac{v_t + v_{gs1}}{r_{o1}} + g_{m1} v_{gs1} = \frac{-v_{gs1}}{r_o} \\ \frac{v_t - v_{gs2}}{r_{o2}} - g_{m2} v_{gs2} = \frac{v_{gs2}}{r_{o3}} \\ i_t = \frac{-v_{gs1}}{r_o} + \frac{v_{gs2}}{r_{o3}} \end{cases}$$

$$\Rightarrow R_{out} = \frac{v_t}{i_t} = \frac{1}{\frac{1}{r_o + r_{o1} + g_{m1} r_{o1} r_{o2}} + \frac{1}{r_{o2} + r_{o3} + g_{m2} r_{o2} r_{o3}}} \quad (1)$$

To get A_v , we need to know $\frac{\partial v_{out}}{\partial v_{in}}$, we can use the AC circuit to obtain the relationship between v_{out} and v_{in}

$$g_{m1} v_{in} + \frac{-v_{gs1}}{r_o} = g_{m1} v_{gs1} + \frac{v_{out} + v_{gs1}}{r_{o1}} = g_{m2} v_{gs2} + \frac{v_{gs2} - v_{out}}{r_{o2}} = \frac{0 - v_{gs2}}{r_{o3}}$$

$$\Rightarrow A_v = \frac{\partial v_{out}}{\partial v_{in}} = \frac{g_{m1}}{\left(\frac{1}{r_o} + \frac{1}{r_{o1}} + g_{m1}\right) \left(\frac{g_{m2} + \frac{1}{r_{o2}}}{(g_{m1} + \frac{1}{r_{o1}})(g_{m2} + \frac{1}{r_{o2}} + \frac{1}{r_{o3}}) r_{o2}} - \frac{\frac{1}{r_{o1}} + \frac{1}{r_{o2}}}{g_{m1} + \frac{1}{r_{o1}}}\right) + \frac{1}{r_{o1}}} \quad (2)$$

From (1) and (2), we can know that when $I_1 = 0.01mA$,

$$r_{o2} = r_{o3} = 2 \times 10^8 \Omega, r_o = r_{o1} = 2.5 \times 10^6 \Omega, g_{m2} = g_{m3} = \sqrt{2} \times 10^{-4} 1/\Omega, g_{m1} = g_m = \sqrt{4.4} \times 10^{-4} 1/\Omega$$

$$\Rightarrow R_{out} = 3.976 \times 10^8 \Omega, A_v = -8.3 \times 10^4$$

From (1) and (2), we can know that when $I_1 = 0.1mA$,

$$r_{o2} = r_{o3} = 2 \times 10^5 \Omega, r_o = r_{o1} = 2.5 \times 10^5 \Omega, g_{m2} = g_{m3} = \sqrt{20} \times 10^{-4} 1/\Omega, g_{m1} = g_m = \sqrt{44} \times 10^{-4} 1/\Omega$$

$$\Rightarrow R_{out} = 1.273 \times 10^7 \Omega, A_v = -8.4 \times 10^3$$

Question 4. Differential Pair (Hard)

Find the intrinsic gain A_v for the amplifier when $I_{SS} = 0.02$ and 0.2mA respectively. (Neglect body effect)

Parameter for NMOS: $V_{THN} = 0.7\text{V}$, $K_n = 110\mu\text{A}/\text{V}^2$, $\lambda = 0.04\text{V}^{-1}$

Parameter for PMOS: $V_{THP} = -0.7\text{V}$, $K_p = 50\mu\text{A}/\text{V}^2$, $\lambda = 0.05\text{V}^{-1}$

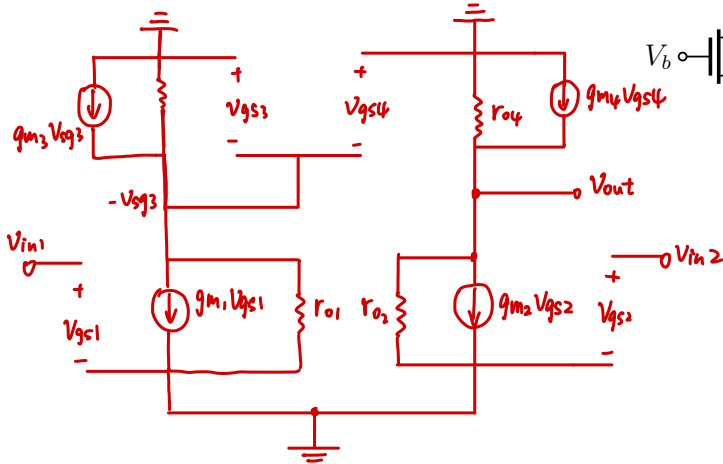
All the size of transistor is $W = 20\mu\text{m}$, $L = 1\mu\text{m}$

Transconductance $g_{mV} = \sqrt{2k'_n \frac{W}{L} I_D}$

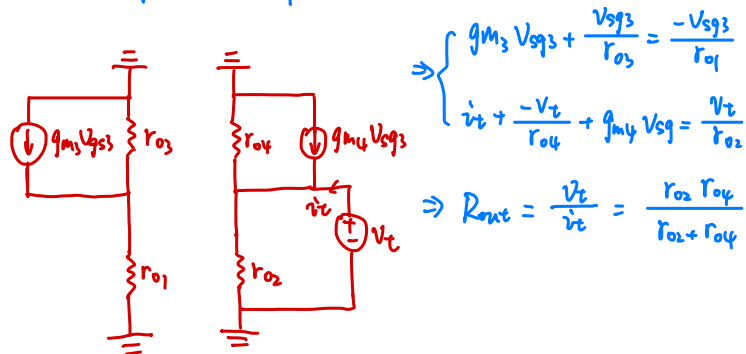
$g_{mP} = \sqrt{2k'_p \frac{W}{L} I_D}$

Output Resistance $r_o = \frac{1}{\lambda I_D}$

Small signal analysis:

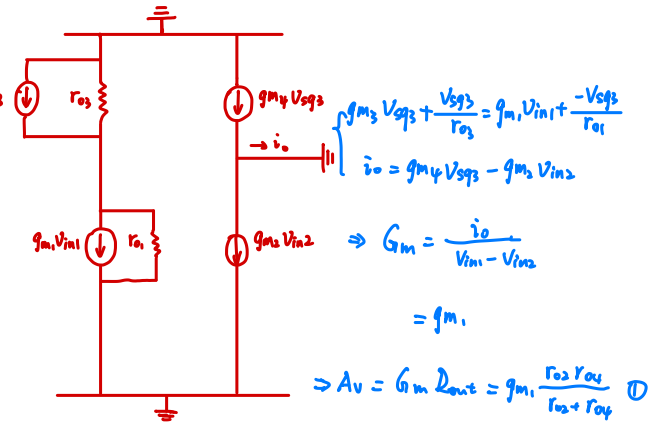


To find the output resistance:



$$\begin{aligned} &\Rightarrow \begin{cases} g_{m3} V_{gs3} + \frac{V_{gs3}}{r_{o3}} = \frac{-V_{gs3}}{r_{o1}} \\ i_t + \frac{-V_t}{r_{o4}} + g_{m4} V_{gs4} = \frac{V_t}{r_{o2}} \end{cases} \\ &\Rightarrow R_{out} = \frac{V_t}{i_t} = \frac{r_{o2} r_{o4}}{r_{o2} + r_{o4}} \end{aligned}$$

To find G_m :



$$\Rightarrow A_v = G_m R_{out} = g_{m1} \frac{r_{o2} r_{o4}}{r_{o2} + r_{o4}} \quad \textcircled{1}$$

From ①. we can know that when $I_{SS} = 0.02\text{mA}$

$$\Rightarrow r_{o2} = 2.5 \times 10^6 \Omega, r_{o4} = 2 \times 10^6 \Omega, g_{m1} = \sqrt{4.4} \times 10^{-4} \text{A/V}$$

$$\Rightarrow A_v = 233.07$$

And when $I_{SS} = 0.2\text{mA}$

$$\Rightarrow r_{o2} = 2.5 \times 10^5 \Omega, r_{o4} = 2 \times 10^5 \Omega, g_{m1} = \sqrt{4.4} \times 10^{-4} \text{A/V}$$

$$\Rightarrow A_v = 73.70$$

Question 5. Differential Pair (Hard)

Find the intrinsic gain A_v for the amplifier when $I_{SS} = 0.02$ and 0.2mA respectively. (Neglect body effect)

Parameter for NMOS: $V_{THN} = 0.7\text{V}$, $K_n = 110\mu\text{A}/\text{V}^2$, $\lambda = 0.04\text{V}^{-1}$

Parameter for PMOS: $V_{THP} = -0.7\text{V}$, $K_p = 50\mu\text{A}/\text{V}^2$, $\lambda = 0.05\text{V}^{-1}$

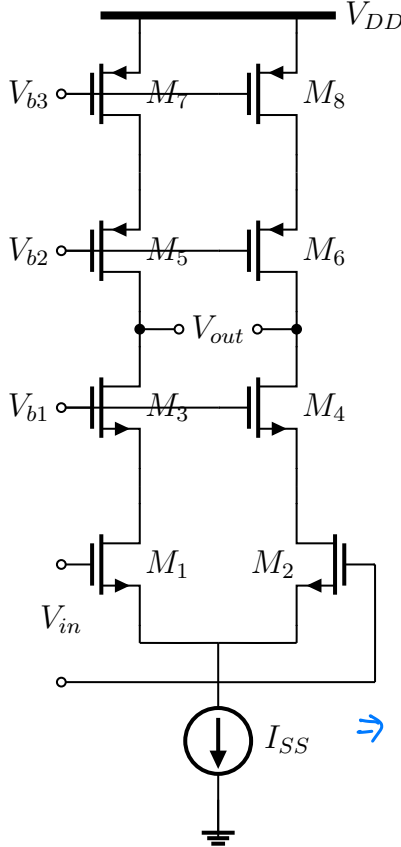
All the size of transistor is $W = 20\mu\text{m}$, $L = 1\mu\text{m}$

Transconductance $g_{mN} = \sqrt{2k'_n \frac{W}{L} I_D}$

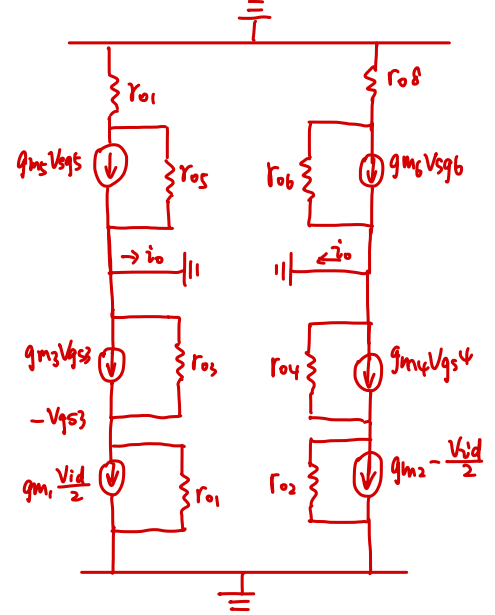
$g_{mP} = \sqrt{2k'_p \frac{W}{L} I_D}$

Output Resistance $r_o = \frac{1}{\lambda I_D}$

Small signal analysis:



To find G_m :



$$\begin{cases} \frac{-V_{gs5}}{r_o} = \frac{V_{gs5}}{r_o} + g_{mP} V_{gs5} \\ \frac{V_{gs3}}{r_o} + g_{mN} V_{gs3} = g_{mN} \frac{V_{id}}{2} + \frac{-V_{gs3}}{r_o} \end{cases}$$

$$\Rightarrow G_m = \frac{r_o g_{mN}^2}{-r_o g_{mN} - 1} = -g_{mN} \text{ (round to } -g_{mN})$$

$$\Rightarrow A_v = R_{out} \cdot G_m = -g_{mN} \cdot \frac{(2 + g_{mP} r_o)(2 + g_{mN} r_o) r_o}{4 + g_{mP} r_o + g_{mN} r_o} \quad (1)$$

From (1), we can know that when $I_{SS} = 0.02\text{mA}$

$$r_{o2} = 2.5 \times 10^6 \Omega, r_{o4} = 2 \times 10^6 \Omega, g_{mN} = \sqrt{4.4} \times 10^{-4} \text{ A/V}, g_{mP} = \sqrt{2} \times 10^{-4} \text{ A/V}$$

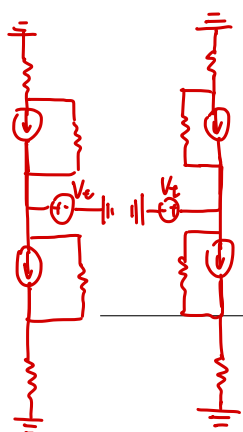
$$\Rightarrow A_v = -8.34 \times 10^4$$

And when $I_{SS} = 0.2\text{mA}$

$$r_{o2} = 2.5 \times 10^5 \Omega, r_{o4} = 2 \times 10^5 \Omega, g_{mN} = \sqrt{4.4} \times 10^{-4} \text{ A/V}, g_{mP} = \sqrt{2} \times 10^{-6} \text{ A/V}$$

$$\Rightarrow A_v = -8.449 \times 10^3$$

To find R_{out} :



$$\frac{V_{gs5}}{r_o} = \frac{V_t - V_{gs5}}{r_o} - g_{mP} V_{gs5}$$

$$\frac{V_{gs3} + V_t}{r_o} + g_{mN} V_{gs3} = \frac{-V_{gs3}}{r_o}$$

$$i_t = \frac{V_{gs5}}{r_o} + \frac{-V_{gs3}}{r_o}$$

$$\Rightarrow R_{out} = \frac{(2 + g_{mP} r_o)(2 + g_{mN} r_o) r_o^2}{(2 + g_{mP} r_o + 2 + g_{mN} r_o) \cdot r_o}$$

$$= \frac{(2 + g_{mP} r_o)(2 + g_{mN} r_o) r_o}{4 + g_{mP} r_o + g_{mN} r_o}$$

Question 6. Common Source with Diode-connected Load (Lunatic)

Consider the circuit of Fig. 2 with $(W/L)_1 = 50/0.5$ and $(W/L)_2 = 10/0.5$. Assume that $\lambda = \gamma = 0$. Then 3 V for V_{DD} , 0.7 V for V_{TH1} , $0.45 \text{ V}^{\frac{1}{2}}$ for γ , and 0.9 V for $2\Phi_F$

- 1) At what input voltage is M_1 at the edge of the triode region? What is the small-signal gain under this condition?
- 2) What input voltage drives M_1 into the triode region by 50mV ? What is the small-signal gain under this condition?

1) Since M_1 is at the edge of the triode region:

$$V_{DS1} = V_{GS1} - V_{TH1}$$

$$V_{out} = V_{in} - 0.7$$

Then we analyze M_2 :

$$\text{Since } V_{GS2} = V_{DS2} \Rightarrow V_{GS2} - V_{TH2} < V_{DS2}$$

$\Rightarrow M_2$ at saturation region

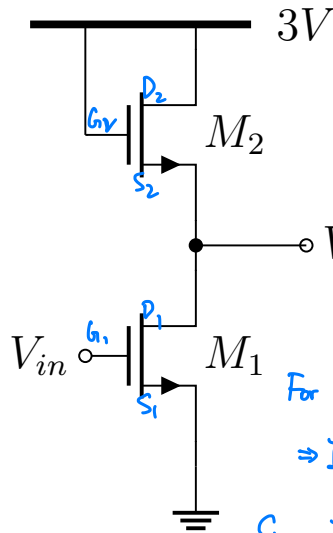
$$\Rightarrow I_{D1} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right)_1 (V_{in} - V_{TH1})^2$$

$$= I_{D2} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right)_2 (V_{DD} - V_{in} + V_{TH2} - V_{TH1})^2$$

$$\Rightarrow 5 (V_{in} - 0.7)^2 = (3 - V_{in})^2 \Rightarrow V_{in} = 1.41 \text{ V}$$

$$\text{Meanwhile } 5 (V_{in} - 0.7)^2 = (2.3 - V_{out})^2 \Rightarrow V_{out} = -\sqrt{5} V_{in} + C$$

$$\Rightarrow A_v = \frac{\partial V_{out}}{\partial V_{in}} = -\sqrt{5} \quad (C \text{ is constant})$$



2) 50mV into triode

$$\Rightarrow V_{out} = 1.41 - 0.7 - 0.05 = 0.66 \text{ V}$$

$$\text{Now for } M_2: V_{GS} = V_{DD} - V_{out} = 2.34 \text{ V} > V_{TH}$$

\Rightarrow saturation region

$$\Rightarrow I_{D2} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right)_2 (V_{GS} - V_{TH})^2$$

For M_1 : triode region

$$\Rightarrow I_{D1} = \mu_n C_{ox} \left(\frac{W}{L}\right)_1 [(V_{in} - V_{TH1}) \cdot V_{out} - \frac{1}{2} V_{out}^2]$$

$$\text{Since } I_{D1} = I_{D2} \Rightarrow \frac{1}{2} (2.34 - 0.7)^2 = 5 [(V_{in} - 0.7) \cdot 0.66 - \frac{1}{2} \cdot 0.66^2]$$

Then we can get that $V_{in} = 1.4375 \text{ V}$

$$\text{Meanwhile } \frac{1}{2} (3 - V_{out} - 0.7)^2 = 5 [(V_{in} - 0.7) \cdot V_{out} - \frac{1}{2} V_{out}^2]$$

$$\Rightarrow V_{in} = \frac{(2.3 - V_{out})^2}{10 V_{out}} + \frac{1}{2} V_{out}$$

$$\Rightarrow A_v = \frac{\partial V_{out}}{\partial V_{in}} = -1.93$$

Question 7. Common Source with Resistive Load (Hell)

Assume $V_{TH} = 0.7 \text{ V}$, $K'_n = 110 \mu\text{A}/\text{V}^2$

Suppose the common-source stage of Fig. 1 is to provide an output swing from 1 V to 2.5 V.

Assume that $(W/L)_1 = 50/0.5$, $R_D = 2 \text{ k}\Omega$, and $\lambda = 0$.

- 1) Calculate the input voltages that yield $V_{out} = 1 \text{ V}$ and $V_{out} = 2.5 \text{ V}$.
- 2) Calculate the drain current and the transconductance of M_1 for both cases.
- 3) How much does the small-signal gain, $g_m R_D$, vary as the output goes from 1 V to 2.5 V? (Variation of small-signal gain can be viewed as nonlinearity.)

1)

$$\textcircled{1} V_{out} = 1 \text{ V} \Rightarrow I_D = \frac{V_{DD} - V_{out}}{R_D} = 1 \text{ mA}$$

Assume MOSFET at saturation:

$$I_D = \frac{1}{2} K'_n \frac{W}{L} (V_{GS} - V_{TH})^2$$

$$= \frac{1}{2} K'_n \frac{W}{L} (V_{in} - 0.7)^2 = 10^{-3}$$

$$\Rightarrow V_{in} = 1.126 \text{ V} \Rightarrow V_{GS} - V_{TH} = 0.426 \text{ V} < V_{DS} = 1 \text{ V}$$

\Rightarrow indeed at saturation \Rightarrow assumption stands

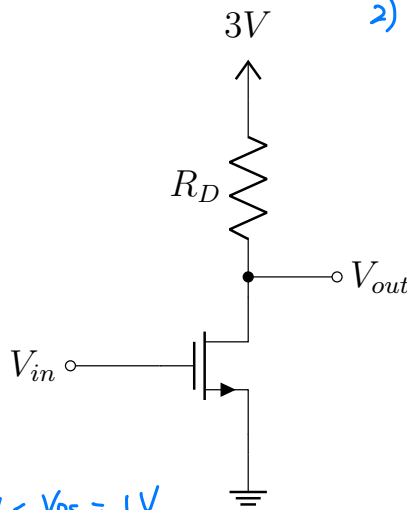
$$\textcircled{2} V_{out} = 2.5 \text{ V} \Rightarrow I_D = \frac{V_{DD} - V_{out}}{R_D} = 0.25 \text{ mA}$$

Assume MOSFET at saturation:

$$I_D = \frac{1}{2} K'_n \frac{W}{L} (V_{GS} - V_{TH})^2 = \frac{1}{2} K'_n \frac{W}{L} (V_{in} - 0.7)^2 = 0.25 \times 10^{-3}$$

$$\Rightarrow V_{in} = 0.9132 \text{ V} \Rightarrow V_{GS} - V_{TH} = 0.2132 \text{ V} < V_{DS} = 2.5 \text{ V}$$

\Rightarrow indeed at saturation \Rightarrow assumption stands



$$2) g_m = \sqrt{2 K'_n \frac{W}{L} I_D}$$

$$\textcircled{1} V_{out} = 1 \text{ V}, I_D = 10^{-3} \text{ A}$$

$$\Rightarrow g_m = \sqrt{2 \times 110 \times 10^{-6} \times 100 \times 10^{-3}} \\ = 4.69 \times 10^{-3} \text{ 1/V}$$

$$\textcircled{2} V_{out} = 2.5 \text{ V}, I_D = 0.25 \times 10^{-4} \text{ A}$$

$$\Rightarrow g_m = \sqrt{2 \times 110 \times 10^{-6} \times 100 \times 2.5 \times 10^{-4}} \\ = 2.34 \times 10^{-3} \text{ 1/V}$$

$$3) R_{out} = r_o \parallel R_D = R_D \text{ (since } \lambda = 0)$$

$$A_v = -g_m R_{out}$$

$$\textcircled{1} V_{out} = 1 \text{ V}, I_D = 10^{-3} \text{ A}, g_m = 4.69 \times 10^{-3} \text{ 1/V}$$

$$\Rightarrow A_v = -9.38$$

$$\textcircled{2} V_{out} = 2.5 \text{ V}, I_D = 0.25 \times 10^{-4} \text{ A}, g_m = 2.34 \times 10^{-3} \text{ 1/V}$$

$$\Rightarrow A_v = -4.68$$